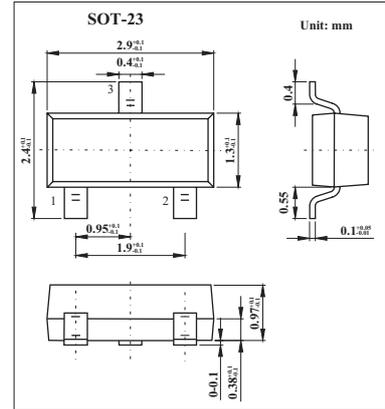


BAV170

■ Features

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Repetitive peak reverse voltage	VRRM			85	V
Continuous reverse voltage	VR			75	V
Continuous forward current	IF	single diode loaded		215	mA
		double diode loaded		125	
Repetitive peak forward current	IFRM			500	mA
Non-repetitive peak forward current	IFSM	square wave; Tj = 25 °C prior to surge			A
		t = 1 μs		4	
		t = 1 ms		1	
		t = 1 s		0.5	
Total power dissipation	Ptot	Tamb = 25		250	mW
Storage temperature	Tstg		-65	+150	°C
Junction temperature	Tj			150	°C
thermal resistance from junction to tie-point	Rth j-t p			360	K/W
thermal resistance from junction to ambient	Rth j-a			500	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Typ	Max	Unit
Forward voltage	V _F	I _F = 1 mA		900	mV
		I _F = 10 mA		1000	
		I _F = 50 mA		1100	
		I _F = 150 mA		1250	
Reverse current	I _R	V _R = 75 V	0.003	5	nA
		V _R = 75 V; T _j = 150 °C	3	80	
Diode capacitance	C _d	f = 1 MHz; V _R = 0;	2		pF
Reverse recovery time	t _{rr}	when switched from I _F = 10 mA to I _R = 10 mA; R _L = 100 Ω ;measured at I _R = 1 mA;	0.8	3	μs

■ Marking

Marking	JXp
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